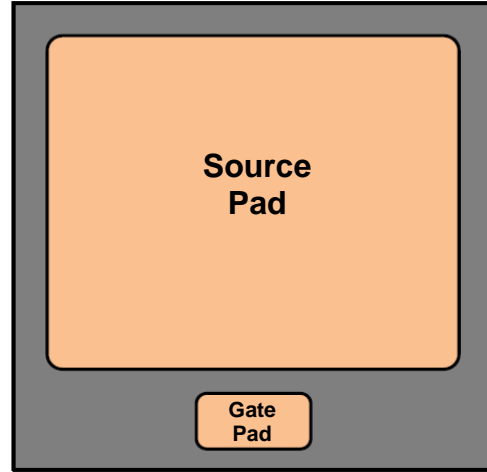


Features

- Low On-Resistance $R_{DS(on)max}$ of 0.080Ω
- Voltage controlled
- Maximum operating temperature of 175°C
- Extremely fast switching not dependent on temperature
- Low gate charge
- Low intrinsic capacitance



Typical Applications

- Over Current Protection Circuits
- DC-AC Inverters
- Switch Mode Power Supplies
- Power Factor Correction Modules
- Motor Drives
- Induction Heating

Part Number	Package
UJN1208Z	Die

Descriptions

United Silicon Carbide, Inc offers the **xJ series** of high-performance SiC normally-on JFET transistors. This series exhibits ultra-low on resistance ($R_{DS(ON)}$) and gate charge (Q_g) allowing for low conduction and switching loss. The device normally-on characteristics with low $R_{DS(ON)}$ at $V_{GS} = 0V$ is also ideal for current protection circuits without the need for active control, as well as for cascode operation.

Absolute Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
Drain-Source Voltage	V_{DS}		1200	V
Gate-Source Voltage	V_{GS}	DC	-20 to +3	V
		AC ⁽¹⁾	-20 to +20	
Continuous Drain Current ⁽²⁾	I_D	$T_C = 25^\circ\text{C}, V_{GS} = 0V$	21	A
Continuous Drain Current ⁽²⁾	I_D	$T_C = 125^\circ\text{C}, V_{GS} = 0V$	13	A
Pulsed Drain Current ⁽²⁾	I_{DM}	$T_j = 125^\circ\text{C}, V_{GS} = 0V$	41	A
		$T_j = 175^\circ\text{C}, V_{GS} = 0V$	35	
Operating and Storage Temperature	T_J, T_{STG}		-55 to 175	°C
Temperature for Soldering	T_L		250	°C

(1) +20V AC rating applies for turn-on pulses <200ns applied with external $R_G > 1\Omega$.

(2) Assumes a maximum junction-to-case thermal resistance of 1.1°C/W

Electrical Characteristics ($T_J = +25^\circ\text{C}$ unless otherwise specified)

Typical Performance - Static

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS} = -20V, I_D = 1mA$	1200			V
Total Drain Leakage Current	I_D	$V_{DS} = 1200V,$ $V_{GS} = -20V, T_J = 25^\circ\text{C}$		40	250	μA
		$V_{DS} = 1200V,$ $V_{GS} = -20V, T_J = 175^\circ\text{C}$		120	750	
Total Gate Leakage Current	I_G	$V_{GS} = -20V, T_J = 25^\circ\text{C}$		0.3	125	μA
		$V_{GS} = -20V, T_J = 175^\circ\text{C}$		3		
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 2V, I_F = 20A,$ $T_J = 25^\circ\text{C}$		67	80	mΩ
		$V_{GS} = 0V, I_F = 15A,$ $T_J = 25^\circ\text{C}$		77	95	
		$V_{GS} = 2V, I_F = 20A,$ $T_J = 175^\circ\text{C}$		200	240	
		$V_{GS} = 0V, I_F = 15A,$ $T_J = 175^\circ\text{C}$		230	285	
Gate Threshold Voltage	$V_{G(th)}$	$V_{DS} = 5V, I_D = 70mA$	-10	-7	-4	V
Gate Resistance	R_G	$V_{GS} = 0V, f = 1MHz$		6		Ω

Typical Performance - Dynamic (Refer to the datasheet of the packaged device UJN1208K)

Parameter	symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Input Capacitance	C_{iss}	$V_{DS} = 100V,$ $V_{GS} = -20V,$ $f = 100kHz$		500		pF
Output Capacitance	C_{oss}			94		
Reverse Transfer Capacitance	C_{rss}			93		
Effective Output Capacitance, Energy Related	$C_{oss(er)}$	$V_{DS} = 0V$ to 600V, $V_{GS} = -20V$		53		pF
Total Gate Charge	Q_G	$V_{DS}=600V, I_D = 20A,$ $V_{GS}=-15V$ to 2.5V		62		nC
Gate-Drain Charge	Q_{GD}			44		
Gate-Source Charge	Q_{GS}			6		
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=600V, I_D=20A,$ Gate Driver =-15V to +5V, $R_{G,EXT} = 2.5\Omega,$ Inductive Load, $T_J = 25^\circ C$		11		ns
Rise Time	t_r			30		
Turn-off Delay Time	$t_{d(off)}$			23		
Fall Time	t_f			26		
Turn-on Energy	E_{ON}			202		
Turn-off Energy	E_{OFF}		210		μJ	
Total Switching Energy	E_{TOTAL}		412			
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=600V, I_D=20A,$ Gate Driver =-15V to +5V, $R_{G,EXT} = 2.5\Omega,$ Inductive Load, $T_J = 150^\circ C$		11		ns
Rise Time	t_r			33		
Turn-off Delay Time	$t_{d(off)}$			22		
Fall Time	t_f			23		
Turn-on Energy	E_{ON}			220		μJ
Turn-off Energy	E_{OFF}			174		
Total Switching Energy	E_{TOTAL}			394		

Typical Performance Diagrams

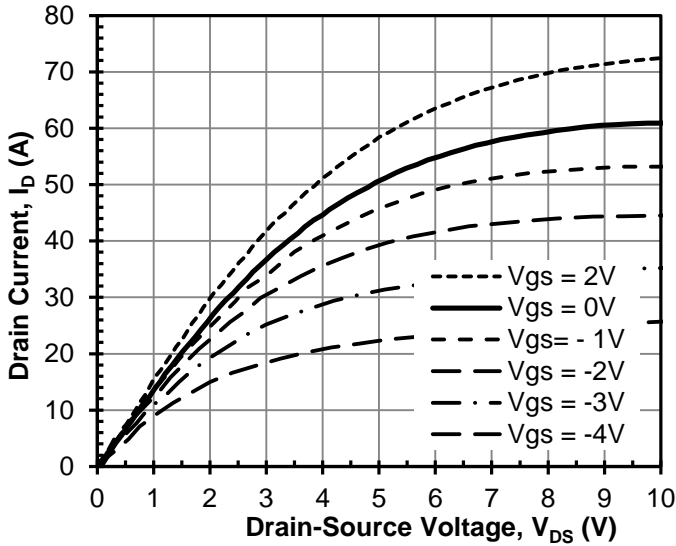


Figure 1 Typical output characteristics at $T_j = 25^\circ\text{C}$

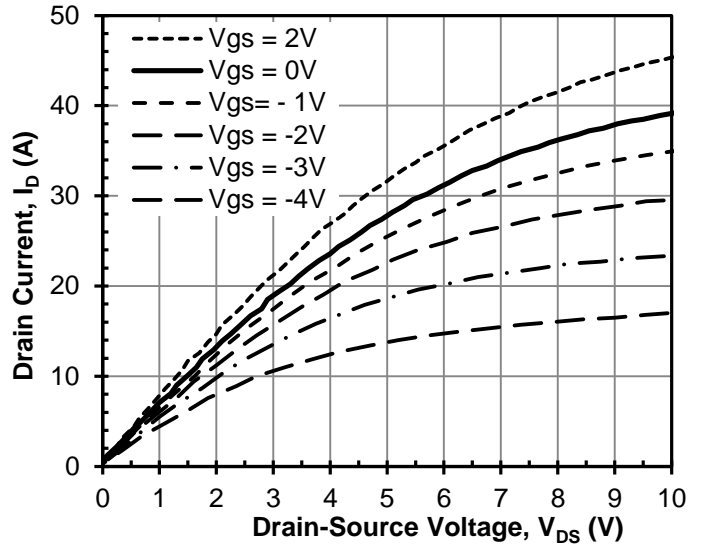


Figure 2 Typical output characteristics at $T_j = 125^\circ\text{C}$

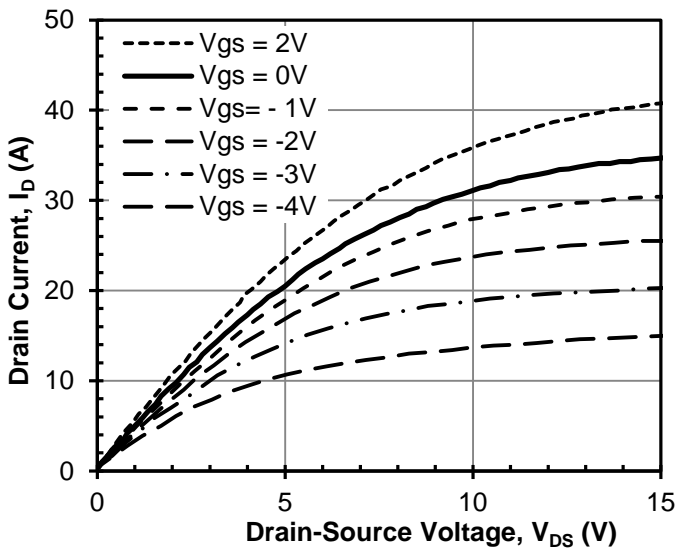


Figure 3 Typical output characteristics at $T_j = 175^\circ\text{C}$

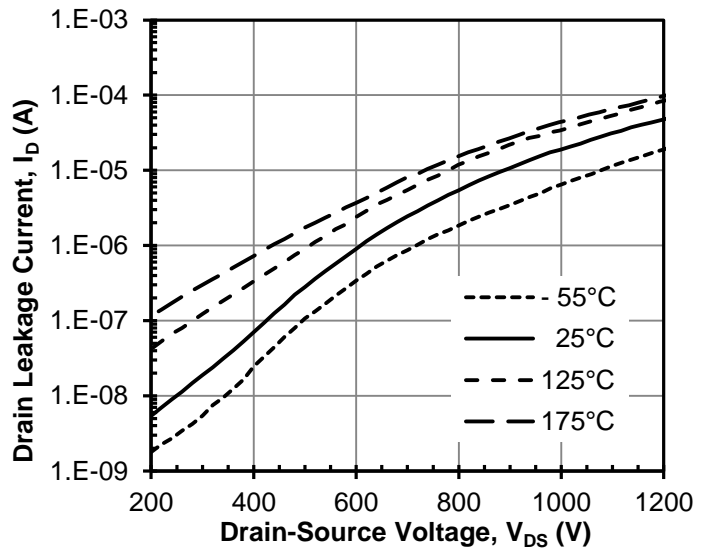


Figure 4 Typical drain-source leakage at $V_{GS} = -20\text{V}$

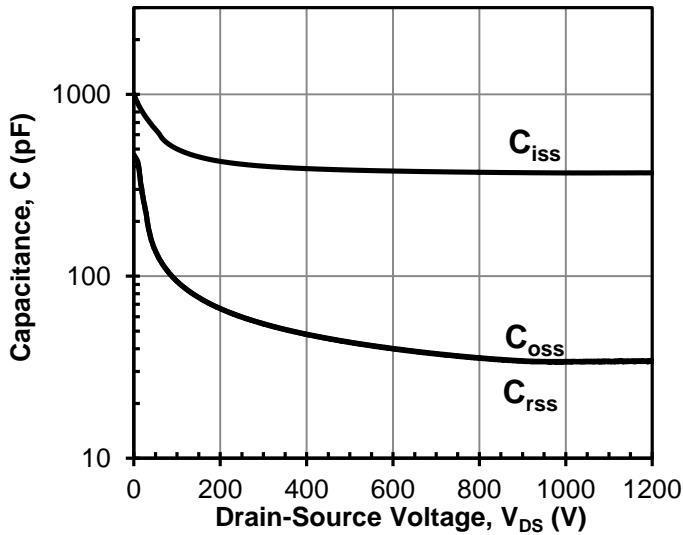


Figure 5 Typical capacitances at 100kHz and $V_{GS} = -20V$

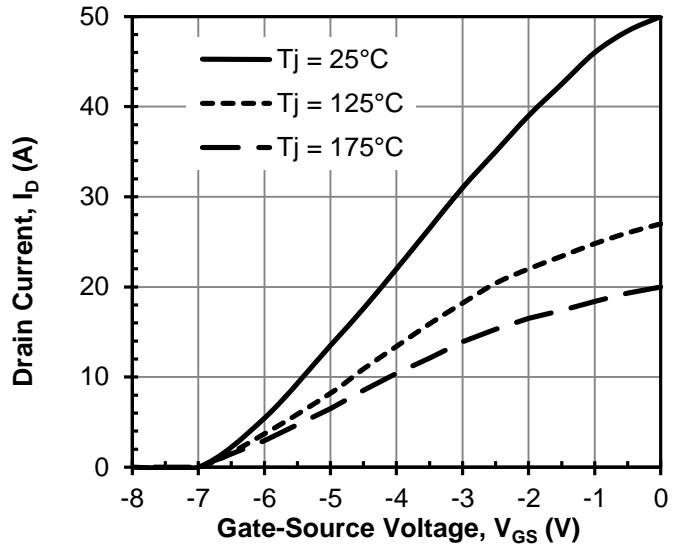


Figure 6 Typical transfer characteristics at $V_{DS} = 5V$

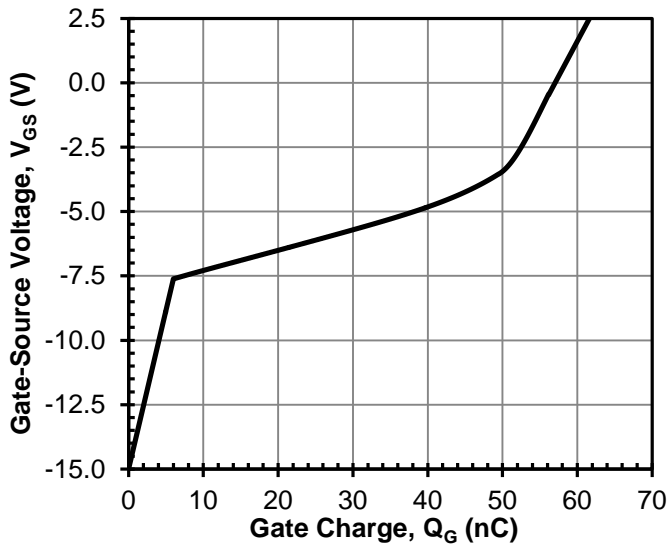


Figure 7 Typical gate charge at $V_{DS} = 600V$ and $I_D = 20A$

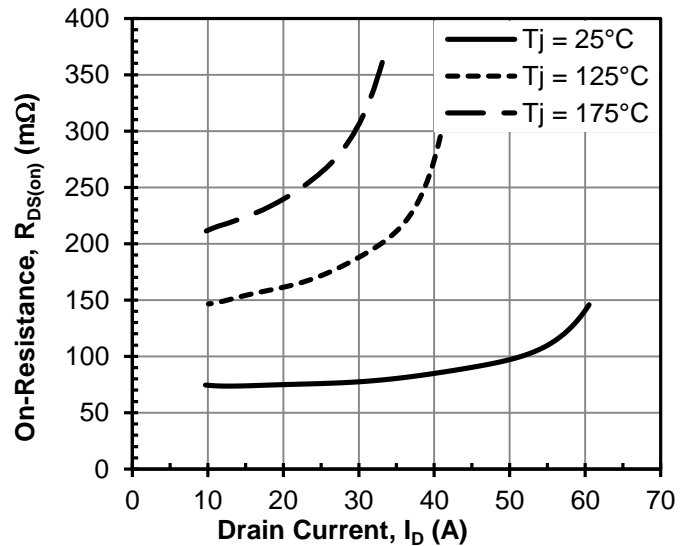


Figure 8 Typical drain-source on-resistance at $V_{GS} = 0V$

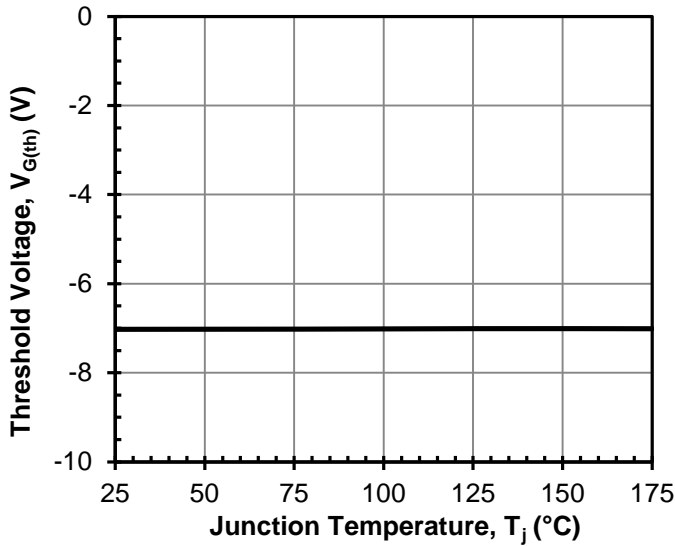


Figure 9 Threshold voltage vs. T_j
at $V_{DS} = 5V$ and $I_D = 70mA$

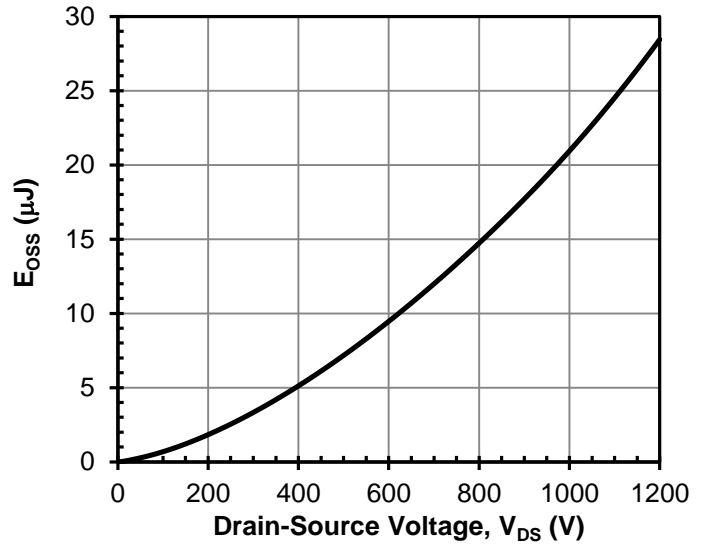


Figure 10 Typical stored energy in C_{OSS}
at $V_{GS} = -20V$

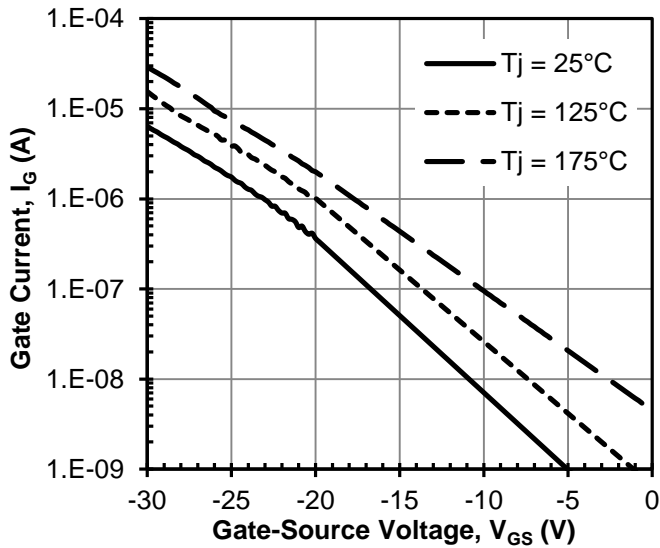


Figure 11 Typical gate leakage current
at $V_{DS} = 0V$

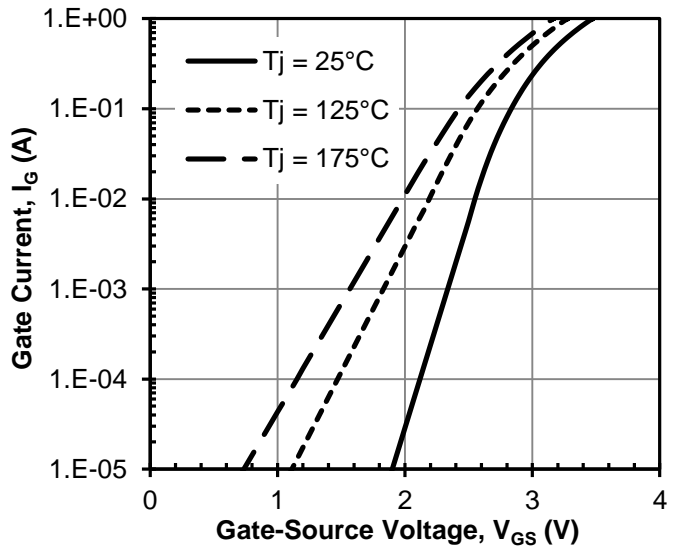
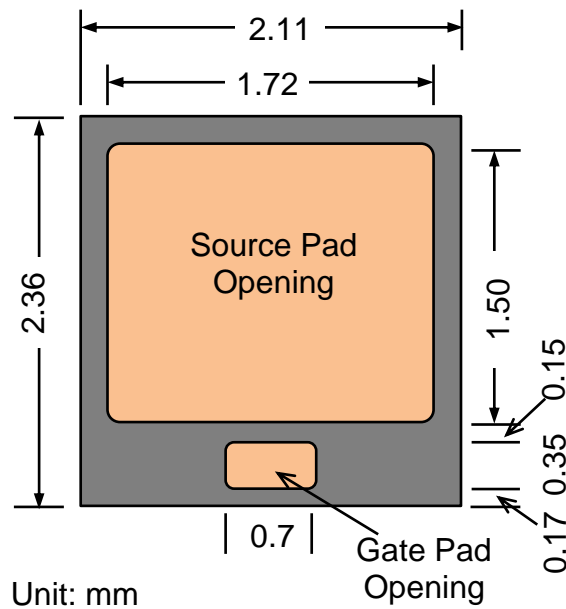


Figure 12 Typical gate forward current
at $V_{DS} = 0V$

Mechanical Characteristics

Parameter	Typical Value	Units
Die Dimensions (L x W)	2.11 x 2.36	mm
Source Pad Metal Dimensions (L x W)	1.72 x 1.50	mm
Gate Pad Metal Dimensions (L x W)	0.7 x 0.35	mm
Source Metallization (Al)	5	μm
Gate Metallization (Al)	5	μm
Backside Drain Metallization (Ti/Ni/Au)	0.07/0.1/0.1	μm
Die Thickness	150	μm

Chip Dimensions



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